TPC Electronics

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TPC Endplate Requirement



ILD LOI constraints: TPC readout endplate < 15% X₀ in z.
 -> a recent PFA study shows that it may be relaxed.
 -> we now set the target at 25% X₀.

-> anyway, "thin" endplate electronics is required.

TPC Electronics Generations

Phase 2 (consolidation) Large Prototype

Semi-Advanced Endplate

Phase 3 (design) Advanced Endplate

Readout cards perpendicular to the pad plane. 4PCA + 4ALTRO chips/Bd.



For GEM/MicroMEGAS pad readout







AFTER (T2K) electronics for MicroMEGAS pad readout



TimePix (pixel readout)

Final target: thin endplate with single-PCB

Candidate: S-ALTRO64 for pad reading





Candidate: TimePix for pixel reading

16ch S-ALTRO Demonstrator (CERN)



- Fabricated May/2011.
- Characterization ongoing.

Reference: "S-ALTRO prototype" 27.07.2010

Power Consumption of S-ALTRO and TPC Advanced Endplate

: 20 (26)[34] mW/ch

- At 10 (20) [40] Ms/s operation,
 - PASA (PreAmp&ShapeAmp) : 8 (8) [8] mW /ch ADC Digital Processor:2(4)[8]mW/chDigital Links:2(4)[8]mW/ch Power Regulators and Aux. : 11 (14)[20] mW/ch
- In total, one channel consumes : 43 (56)[79] mW/ch
- When the pad pitch is 1mm x 4mm, power density will be : 11 (14) [20] kW/m²
- With power pulsing of 1.5% duty cycle

: 160 (210)[300] W/m²

- This number is comparable with ALICE TPC frontend. Difference: LCTPC endplate material budget <25% X₀, and we need different cooling mechanism -> CO₂ cooling.
- Half Cylinder of ILD TPC with inner Φ =0.65m and outer Φ =3.6m : 1.5 (2.1) [3.0] kW of which 88 (81) [72] % is analog.







↑ LCTPC AEP / ALICE TPC \downarrow



ALICE TPC Electronics

- PC board ~150µm Cu (0.1 X₀)
- 22mW / cm² ⇒ 220W / m²
- 0.3mm copper plate (0.2 X₀)

Future S-ALTRO idea

(Essentially, only after evaluation of 16ch S-ALTRO demonstrator, we can discuss final S-ALTRO design.)

Optimization of pipelined-ADC or replacing it with different architecture (SAR ADC).

Challenge: 4mW/ch @ 40Msps



G BOO ASSCC ASSSCC

Tuning of Front-end circuit power.

Even with these power reduction, power pulsing is still necessary. Power management with multiple power domains for power pulsing:

- Analog: Reduce current via bias control.
- ADC: Stop clock and reduce current.
- Digital: Reduce Vdd to minimum or 0V.

Advanced Endplate Test Board

We have constructed Advanced-Endplate "test boards" to test:

- Liquid CO₂ cooling
 - Temperature of ASICs and pads.
- Power pulsing condition
 - Power line stability
 - Noise effect to analog signals
 - PP in strong magnetic field
- Fabricationability
 - Many SMT devices on a PCB

For these studies, surface-mounted FPGAs and ADCs are mounted instead of the future S-ALTRO.







Advanced Endplate Test Board (parts-side view)



Advanced Endplate Test Board (SModule Zoom-up)



Advanced Endplate Test Board (Pad side)

Pads are prepared on the AEP test board and connected to FPGA pins in order to observe temperature change of pads, which can affect gas volume temperature. Some pads are connected to ADC inputs via charge amps (OPamps), with which we aim to observe power-pulsing effect to analog circuits.





2P CO₂ blow cooling test bench

Blow system of 2 phase CO2 cooling was setup at KEK by the CO₂ cooling research group. The AEP TB test with the system will be performed in FY2011.



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First setup of TB for CO₂ blow system

With simple cooling device attached on top side, temperature data will be taken under CO₂ cooling condition.





SModule power consumption when w/o power pulsing



Simulation study of AEP test board



Simulation tasks:

- Include precise PCB model.
- The whole PCB data is too large to be processed by a heat simulator.
- --> trying simplification technique.
- The simulation shown here is "static".
 --> go transient simulation.

(heat capacity information is needed)



establish heat simulation method



Ideal shape of AEP cooling

	Layer	struct	ure	material (μm)	plate (µm)	grade	比誘電率	誘電正接	残御率 (96)	finish (µm)
	-	SR		30		SR	3.7	0.02		30
	Lay1			5	15					20
		~~~~ ~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~		pp60+1		FR5	4.3	0.022		70
	Lay2			18	15					35
				core100		FR5	4.3	0.022		100
	Lay3			35						32
		~~~~~~	~ ~~~~	pp150+1		FR5	4.3	0.022		160
	Lay4			35						32
	S			core100		FR5	4.3	0.022		100
	Lay5			35						32
		~~~~~~	~ ~~~~	pp150*1		FR5	4.3	0.022		160
	Lay6			35						32
				core100		FR5	4.3	0.022		100
	Lay7			35						32
		~~~~~~	~ ~~~~	pp150+1		FR5	4.3	0.022		160
_	Lay8			35						32
				core100		FR5	4.3	0.022		100
	Lay9			18	15					35
and the second se		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~		pp60+1		FR5	4.3	0.022		70
nad laver	Lay10			5	15				2	20
pad layer		SR		30		SR	3.7	0.02		30

AEP TB layer structure

put cooling device in between PCB layers to block heat diffusion from electronics to gas volume



Channels are created by etching, then two Cu plates are bonded. Good thermal contact, but possible only up to 5 atm according to a company. Channels are created by pipes, then sandwitched by two Cu plates. Good thermal contact, endurable to high pressure, but thick material.

Thin and long piping → dry out!



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Thin, endurable to high pressure, but how is thermal contact?

Channels are created by pipes, then put in between

PCB layers.

How to branch?

looking for good industrial choice > 50atm

Daughter-board option for TPC readout (Semi-AEP idea by Lund group)



AFTER-based electronics

• 1 FEM, 6 FECs, 24 chips :1728 ch

- 12-bit ADC, 6 channels multiplexed
- Zero Suppression capability (FPGA)
- $-\sim 14-25$ mW/channel





fits 7 module micromegas for the large prototype



Single-module operation with 5GeV electron beam in B=1T





power pulsing under 5T is planned

8 Ingrid TimePix chips: Octapos

<u>TimePix chip</u>

65 000 digital pixels (55 μm x 55 μm) with "single" time and TOT measurement, an Ingrid MicroMEGAS, the resistive Si layer to protect Timepix. Capability to detect single electron. Only one hit for a cell.





- TimePix1 (CMOS 250nm) is not designed to be power-pulsed.
- * TimePix3 (CMOS 130nm) will have a power pulsing strategy. (submit: 2012)

Summary

- Technologies for realization of the advanced endplate are being prepared.
- 16ch S-ALTRO demonstrator chips were fabricated and their characterization is being performed. Depending on the results, final S-ALTRO strategy will be discussed.
- Test of CO₂ cooling and power pulsing is going to be performed using advanced endplate test board at KEK in 2011.
- Some semi-advanced endplate plans are presented.